

Product Overview

NXH80B120L2Q0: Power Integrated Module, Dual Boost, 1200 V, 40 A IGBT + 1200 V, 30 A Si Diode

For complete documentation, see the data sheet.

The NXH80B120L2Q0SG is a power module containing a dual boost stage consisting of two 40A/1200V IGBTs, two 30A/1200V silicon diodes, and two 25A/1600V anti-parallel diodes for the IGBTs. Two additional 25A/1600V bypass rectifiers used for inrush current limit are included. An on-board thermistor is included.

Features

- IGBT Specifications: $V_{CE(SAT)} = 2.2\text{ V}$, $ESW = 2830\text{ }\mu\text{J}$
- 25 A / 1600 V Bypass and Anti-parallel Diodes

- Si Rectifier Specification: $V_F = 2.4\text{ V}$, $IRRM = 53\text{ A}$
- Solderable Pins
- Dual Boost 40 A / 1200 V IGBT + Si Rectifier Module
- Thermistor

Applications

- Solar Inverter Boost Stage

Benefits

- Fast IGBT with low $V_{CE(SAT)}$ for high efficiency
- Low V_F bypass diodes for excellent efficiency in bypass mode
- Si Diode for moderate speed switching
- Easy mounting

End Products

- Solar Inverter
- UPS

For more information please contact your local sales support at www.onsemi.com.

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